

Robert Piotr SarzaÅ,a

List of Publications by Year in descending order

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159
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159
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citing authors

#	ARTICLE	IF	CITATIONS
1	Cavity designs for nitride VCSELs with dielectric DBRs operating efficiently at different temperatures. Optics and Laser Technology, 2020, 132, 106482.	2.2	6
2	Numerical model for small-signal modulation response in vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 2020, 53, 345101.	1.3	4
3	Impact of an Antiresonant Oxide Island on the Lasing of Lateral Modes in VCSELs. Materials, 2020, 13, 2195.	1.3	2
4	Numerical Investigation of the Impact of ITO, AlInN, Plasmonic GaN and Top Gold Metalization on Semipolar Green EELs. Materials, 2020, 13, 1444.	1.3	4
5	Influence of Various Bottom DBR Designs on the Thermal Properties of Blue Semiconductor-Metal Subwavelength-Grating VCSELs. Materials, 2019, 12, 3235.	1.3	6
6	Influence of Resonator Length on Performance of Nitride TJ VCSEL. IEEE Journal of Quantum Electronics, 2019, 55, 1-9.	1.0	5
7	Monolithic High Contrast Grating Nitride-Based VECSEL. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-8.	1.9	0
8	Wpływ niedokładności wykonania wybranych elementów azotkowego lasera VCSEL na jego charakterystyki emisyjne. Przegląd Elektrotechniczny, 2019, 1, 129-132.	0.1	0
9	Quantum-Cascade Vertical-Cavity Surface-Emitting Laser (QC-VCSEL). , 2018, , .		1
10	Thermal properties of GaN-based semiconductor-metal subwavelength grating VCSELs and novel current injection scheme. Journal Physics D: Applied Physics, 2018, 51, 285102.	1.3	10
11	Concept of the CW GaN-based VECSEL. , 2018, , .		2
12	Impact of the top DBR in GaAs-based VCSELs on the threshold current, oxide-aperture diameter, and the cavity photon lifetime. , 2018, , .		1
13	Optical simulations of blue and green semipolar InGaN/GaN lasers. , 2018, , .		3
14	Metalized monolithic high-contrast grating as a mirror for GaN-based VCSELs. , 2018, , .		0
15	Projekt azotkowego lasera VCSEL z bezpośrednim wstrzykiwaniem prądu do obszaru czynnego. Przegląd Elektrotechniczny, 2018, 1, 3-6.	0.1	0
16	Influence of the number of pairs in the top DBR and carrier injection efficiency on the nitride VCSEL performance. , 2018, , .		0
17	Subwavelength grating as both emission mirror and electrical contact for VCSELs in any material system. Scientific Reports, 2017, 7, 40348.	1.6	16
18	Impact of thermal crosstalk between emitters on power roll-over in nitride-based blue-violet laser bars. Semiconductor Science and Technology, 2017, 32, 025008.	1.0	1

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19	Modeling of optical and electrical confinements in nitride VCSELs. , 2017, , .		1
20	Modelling of the modulation properties of arsenide and nitride VCSELs. , 2017, , .		0
21	Numerical study of VCSELs for generation of mid-infrared radiation. , 2017, , .		0
22	Impact of AlN-aperture on optical and electrical properties of nitride VCSEL. Optical and Quantum Electronics, 2017, 49, 1.	1.5	7
23	Początek i rozwój p-przewodnikowych laserów VCSEL. Przegląd Elektrotechniczny, 2017, 1, 3-10.	0.1	0
24	Impact of structure mounting of nitride laser bars on the emitted optical power. , 2016, , .		0
25	Designing of TJ VCSEL based on nitride materials. , 2016, , .		2
26	Simulation of carrier and power losses in semiconductor disk lasers. , 2016, , .		0
27	Numerical model of capacitance in vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 2016, 49, 175104.	1.3	17
28	Development of the Nitride Laser Diode Arrays for Video and Movie Projectors. MRS Advances, 2016, 1, 103-108.	0.5	6
29	Analysis of Threshold Currents and Transverse Modes in Nitride VCSELs With Different Resonators. IEEE Journal of Quantum Electronics, 2016, 52, 1-7.	1.0	8
30	Impact of AlN-aperture on optical and electrical properties on nitride VCSEL , 2016, , .		0
31	Numerical analysis of suppression of the higher order modes in nitride VCSELs using an inverted surface relief. , 2016, , .		0
32	Single-mode enhancement in coupled-cavity quantum cascade lasers. Proceedings of SPIE, 2016, , .	0.8	1
33	Comprehensive and fully self-consistent modeling of modern semiconductor lasers. Journal of Semiconductors, 2016, 37, 024001.	2.0	11
34	Numerical investigation of an impact of a top gold metallization on output power of a p-up III-N-based blue-violet edge-emitting laser diode. Opto-electronics Review, 2015, 23, .	2.4	4
35	Numerical study of the influence of pumping beam parameters on VCSEL performance. , 2015, , .		0
36	VCSEL modeling with self-consistent models: From simple approximations to comprehensive numerical analysis. , 2015, , .		3

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37	Direct Au–Au bonding technology for high performance GaAs/AlGaAs quantum cascade lasers. Optical and Quantum Electronics, 2015, 47, 893-899.	1.5	14
38	Electrically Pumped Vertical-External-Cavity Surface-Emitting Lasers With Patterned Tunnel Junction for Single Transversal-Mode Emission. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 485-492.	1.9	1
39	Impact of Heat Spreaders on Thermal Performance of III-N-Based Laser Diode. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2015, 5, 474-482.	1.4	5
40	Single and double oxidations in a 980-nm VCSEL: impact on certain electrical and optical properties. , 2015, , .		1
41	Double high refractive-index contrast grating VCSEL. Proceedings of SPIE, 2015, , .	0.8	1
42	Comparative analysis of GaAs- and GaSb-based active regions emitting in the mid-infrared wavelength range. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2015, 63, 597-603.	0.8	2
43	Transverse-mode selectivity in antimonide-based vertical-cavity surface-emitting lasers. , 2015, , .		1
44	Modeling of multi-mode properties in high-power VCSELs. , 2015, , .		0
45	Double-diamond high-contrast-gratings vertical external cavity surface emitting laser. Journal Physics D: Applied Physics, 2014, 47, 065104.	1.3	38
46	Switchable double wavelength generating vertical external cavity surface-emitting laser. Optics Express, 2014, 22, 6447.	1.7	12
47	Numerical Analysis of Mode Discrimination by Intracavity Patterning in Long-Wavelength Wafer-Fused Vertical-Cavity Surface-Emitting Lasers. IEEE Journal of Quantum Electronics, 2014, 50, 1-9.	1.0	9
48	Effect of Relief Aperture on Single-Fundamental-Mode Emission of 1.3- μ m GaInNAs GaAs-Based VCSELs. IEEE Journal of Quantum Electronics, 2014, 50, 1-8.	1.0	3
49	Spatial mode discrimination in anti-guided arrays of long-wavelength VCSELs. Proceedings of SPIE, 2014, , .	0.8	0
50	Comparison of spatial anti-guided mechanism in single emitter VCSELs and VCSEL arrays. Proceedings of SPIE, 2014, , .	0.8	0
51	Coaxial tunnel junctions: a novel approach to reduce the current crowding effect in electrically-pumped VCSELs. Proceedings of SPIE, 2014, , .	0.8	1
52	Optimization of GaInNAs quantum-well vertical-cavity surface-emitting laser emitting at 2.33 μ m. Applied Physics A: Materials Science and Processing, 2014, 115, 961-969.	1.1	2
53	A Possibility to achieve emission in the mid-infrared wavelength range from semiconductor laser active regions. , 2014, , .		3
54	Numerical simulation of 1.3- μ m vertical-external-cavity surface-emitting lasers. , 2014, , .		0

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55	Coupled-cavity VCSELs: numerical analysis of physical phenomena. , 2014, , .		0
56	Influence of Pumping Beam Width on Vecsel Output Power. International Journal of Electronics and Telecommunications, 2014, 60, 239-245.	0.6	5
57	Inverted-relief cavity used in VCSELs to suppress higher-order transverse modes. Photonics Letters of Poland, 2014, 6, .	0.2	0
58	Intra-cavity patterning - new method of single mode emission enhancement. Photonics Letters of Poland, 2014, 6, .	0.2	0
59	Thermal management of GaInNAs/GaAs VCSELs. Opto-electronics Review, 2013, 21, .	2.4	9
60	Thermal crosstalk in arrays of III-N-based Lasers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2013, 178, 1395-1402.	1.7	27
61	Numerical analysis of optically pumped VCSELs. , 2013, , .		5
62	Automated self-consistent approach to modeling of photonic devices. , 2013, , .		2
63	Spatial-Mode Discrimination in Guided and Antiguided Arrays of Long-Wavelength VCSELs. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1-10.	1.9	5
64	A method used to enhance mode selectivity of VCSELs with large oxide apertures. , 2013, , .		0
65	A method used to overcome polarization effects in semi-polar structures of nitride light-emitting diodes emitting green radiation. Applied Physics A: Materials Science and Processing, 2013, 113, 801-809.	1.1	7
66	Photonic Crystal VCSELs: Detailed Comparison of Experimental and Theoretical Spectral Characteristics. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1-8.	1.9	10
67	Optimization of Single-Mode Photonic-Crystal Results in Limited Improvement of Emitted Power and Unexpected Broad Range of Tuning. Journal of Lightwave Technology, 2013, 31, 1360-1366.	2.7	3
68	Numerical analysis of photonic-crystal VCSELs. , 2013, , .		0
69	GaInNAs quantum-well vertical-cavity surface-emitting lasers emitting at 2.33 μ m. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2013, 61, 737-744.	0.8	3
70	How to control single mode emission of VCSEL arrays?. , 2013, , .		0
71	Why photonic-crystal VCSELs do not provide high power emission in the single-mode regime?. , 2013, , .		0
72	Simplified thermal analysis of impact of diamond heat spreader on InGaN laser diode arrays. , 2013, , .		0

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73	Simulation of 1550-nm diamond VECSEL with high contrast grating. Proceedings of SPIE, 2012, , .	0.8	2
74	Three-dimensional simulation of 1300-nm AlGaInAs VCSEL arrays. Proceedings of SPIE, 2012, , .	0.8	0
75	An attempt to design long-wavelength ($\approx 2 \mu\text{m}$) InP-based GaInNAs diode lasers. Applied Physics A: Materials Science and Processing, 2012, 108, 521-528.	1.1	10
76	A new structure of nitride light-emitting diodes without polarization effects. Physica B: Condensed Matter, 2012, 407, 3960-3964.	1.3	0
77	Highly doped GaN: a material for plasmonic claddings for blue/green InGaN laser diodes. Proceedings of SPIE, 2012, , .	0.8	12
78	Numerical Self-Consistent Analysis of VCSELS. Advances in Optical Technologies, 2012, 2012, 1-17.	0.8	23
79	Precise Lateral Mode Control in Photonic Crystal Vertical-Cavity Surface-Emitting Lasers. IEEE Journal of Quantum Electronics, 2011, 47, 1291-1296.	1.0	16
80	GaAs/AlGaAs photonic crystals for VCSEL-type semiconductor lasers. Opto-electronics Review, 2011, 19, .	2.4	3
81	Current spreading modification to enhance single-fundamental-mode VCSEL operation at higher temperatures. Opto-electronics Review, 2011, 19, .	2.4	0
82	Investigation of temperature characteristics of modern InAsP/InGaAsP multi-quantum-well TJ-VCSELS for optical fibre communication. Opto-electronics Review, 2011, 19, .	2.4	11
83	Comparative analysis of lasing performance of oxide-confined and H^+ -proton-implanted vertical-cavity surface-emitting diode lasers. Applied Physics A: Materials Science and Processing, 2011, 102, 359-366.	1.1	2
84	Structure modifications of oxide-confined GaInNAs VCSELS for the second-generation optical-fibre communication. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1601-1604.	0.8	0
85	Simulation of an operation of zinc oxide light-emitting diodes. Microwave and Optical Technology Letters, 2011, 53, 2086-2090.	0.9	4
86	Temperature increase within quantum-cascade lasers originating from their incomplete soldering. Photonics Letters of Poland, 2011, 3, .	0.2	3
87	Pulse-regime single-mode operation of antiwaveguide photonic-crystal 1300-nm VCSEL. , 2010, , .		0
88	Enhanced single-fundamental LP01 mode operation of 650-nm GaAs-based GaInP/AlGaInP quantum-well VCSELS. Applied Physics A: Materials Science and Processing, 2010, 98, 651-657.	1.1	7
89	Physics of mode selectivity of vertical-cavity surface-emitting diode lasers. Journal of Applied Physics, 2010, 108, 044501.	1.1	5
90	Photonic crystal used to increase extraction efficiency of ZnO light-emitting diodes. Photonics Letters of Poland, 2010, 2, .	0.2	0

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91	Microthermography of diode lasers: The impact of light propagation on image formation. Journal of Applied Physics, 2009, 105, 014502.	1.1	16
92	Optimal photonic-crystal parameters assuring single-mode operation of 1300 nm AlInGaAs vertical-cavity surface-emitting laser. Journal of Applied Physics, 2009, 105, 093102.	1.1	15
93	Room-temperature continuous-wave operation of the In(Ga)As/GaAs quantum-dot VCSELs for the 1.3 μm optical-fibre communication. Semiconductor Science and Technology, 2009, 24, 055003.	1.0	22
94	Strong modes discrimination and low threshold in cw regime of 1300 nm AlInGaAs/InP VCSEL induced by photonic crystal. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1396-1403.	0.8	11
95	Structure optimisation of modern GaAs-based InGaAs/GaAs quantum-dot VCSELs for optical fibre communication. Opto-electronics Review, 2009, 17, .	2.4	3
96	Temperature reduction in vertical-external-cavity surface-emitting-lasers (VECSEL) active region. , 2009, , .		1
97	Analysis of excitation of higher-order transverse modes in large-size oxide-confined VCSELs. , 2009, , .		0
98	Threshold characteristics of bottom-emitting long wavelength VCSELs with photonic-crystal within the top mirror. Optical and Quantum Electronics, 2008, 40, 149-154.	1.5	1
99	Investigation of operational characteristics and possibility of obtaining highly detuned GaInNAsSb VCSEL. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 445-448.	0.8	0
100	Threshold analysis of highly detuned long-wavelength GaAs-based GaInNAsSb/GaNAsQWVCSELs. Microelectronics Journal, 2008, 39, 641-643.	1.1	1
101	Tuning effects in optimisation of GaAs-based InGaAs/GaAs quantum-dot VCSELs. Optics Communications, 2008, 281, 3163-3170.	1.0	6
102	Computer simulation of an operation of the GaInP/AlGaInP QW VCSELs: Excitation of various transverse LP _{ij} modes. Microelectronics Journal, 2008, 39, 638-640.	1.1	3
103	Analysis of anticipated performance of 650-nm GaInP/AlGaInP quantum-well GaAs-based VCSELs at elevated temperatures. Opto-electronics Review, 2008, 16, .	2.4	5
104	Structure optimisation of short-wavelength ridge-waveguide InGaN/GaN diode lasers. Opto-electronics Review, 2008, 16, .	2.4	3
105	Performance Characteristics of GaAs-Based Oxide-Confined In(Ga)As/GaAs Quantum-Dot Vertical-Cavity Surface-Emitting Diode Lasers. , 2008, , .		1
106	Comparative Analysis of Thermal Properties of Various Quantum-Cascade Lasers. , 2008, , .		0
107	Visualization of heat flows in high-power diode lasers by lock-in thermography. Applied Physics Letters, 2008, 92, 103513.	1.5	7
108	Comparison of the room-temperature threshold operation of index- and gain-guided oxide-confined VCSELs. , 2008, , .		0

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109	Unusual transverse-mode selectivity in some detuned VCSELs. , 2008, , .		0
110	Thermal Imaging of Actively Cooled High-Power Laser Bars. , 2007, , .		1
111	Self-consistent model of 650 nm GaInP/AlGaInP quantum-well vertical-cavity surface-emitting diode lasers. Semiconductor Science and Technology, 2007, 22, 593-600.	1.0	25
112	Optimization of oxide-confined vertical-cavity surface-emitting diode lasers. Semiconductor Science and Technology, 2007, 22, 113-118.	1.0	6
113	GaInNAsSb/GaNAs quantum-well VCSELs: Modeling and physical analysis in the 1.50~1.55~µm wavelength range. Journal of Applied Physics, 2007, 101, 073103.	1.1	3
114	Optimal Designs of Telecommunications Oriented Photonic-Crystal VCSELs. , 2007, , .		0
115	Comparison of Usability of Oxide Apertures and Photonic Crystals Used to Create Radial Optical Confinements in 650-nm GaInP VCSELs. IEEE Journal of Quantum Electronics, 2007, 43, 1041-1047.	1.0	10
116	Exactness of simplified scalar optical approaches in modelling a threshold operation of possible nitride vertical-cavity surface-emitting diode lasers. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 3562-3573.	0.8	4
117	Comparative Analysis of Various Designs of Oxide-Confined Vertical-Cavity Surface-Emitting Diode Lasers. , 2006, , .		0
118	Transient thermal properties of high-power diode laser bars. Applied Physics Letters, 2006, 89, 263506.	1.5	42
119	<title>Physics of an operation of vertical cavity surface emitting lasers with oxide apertures</title>. , 2006, , .		0
120	Structure Optimisation of a Possible 1.5-µm GaAs-based Vertical-cavity Surface-emitting Laser Diode with the GaInNAsSb/GaNAs Quantum-well Active Region. Optical and Quantum Electronics, 2006, 38, 293-311.	1.5	1
121	Physical Analysis of a Possibility to Reach the 1.30-µm Emission from the GaAs-Based VCSELs with the InGaAs/GaAs Quantum-Well Active Regions and the Intentionally Detuned Optical Cavities. Optical and Quantum Electronics, 2006, 38, 325-337.	1.5	1
122	Separate-confinement-oxidation vertical-cavity surface-emitting laser structure. Journal of Applied Physics, 2006, 99, 123110.	1.1	16
123	Methods to enhance mode selectivity of higher-output vertical-cavity surface-emitting diode lasers. , 2005, , .		0
124	The modified k·p method to investigate polarization effects in nitride quantum-well devices. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 25, 504-514.	1.3	7
125	Designing strategy to enhance mode selectivity of higher-output oxide-confined vertical-cavity surface-emitting lasers. Applied Physics A: Materials Science and Processing, 2005, 81, 275-283.	1.1	27
126	Optimization of 1.3 µm GaAs-based oxide-confined (GaIn)(NAs) vertical-cavity surface-emitting lasers for low-threshold room-temperature operation. Journal of Physics Condensed Matter, 2004, 16, S3121-S3140.	0.7	59

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127	Fully self-consistent threshold model of one-dimensional arrays of edge-emitting nitride diode lasers. Semiconductor Science and Technology, 2004, 19, 997-1004.	1.0	4
128	Optimisation of GaAs-based (GaIn)(NAs)//GaAs vertical-cavity surface-emitting diode lasers for high-temperature operation in 1.3- μ m optical-fibre communication systems. IEE Proceedings: Optoelectronics, 2004, 151, 417-420.	0.8	2
129	Comprehensive self-consistent three-dimensional simulation of an operation of the GaAs-based oxide-confined 1.3- μ m quantum-dot (InGa)As/GaAs vertical-cavity surface-emitting lasers. Optical and Quantum Electronics, 2004, 36, 331-347.	1.5	23
130	Cascade nitride VCSEL designs with tunnel junctions. Applied Physics A: Materials Science and Processing, 2004, 78, 315-322.	1.1	2
131	Modeling of the threshold operation of 1.3- μ m GaAs-based oxide-confined (InGa)As-GaAs quantum-dot vertical-cavity surface-emitting lasers. IEEE Journal of Quantum Electronics, 2004, 40, 629-639.	1.0	29
132	A new approach to improve mode selectivity of higher output oxide-confined vertical-cavity surface-emitting lasers. Semiconductor Science and Technology, 2004, 19, 1122-1124.	1.0	3
133	Threshold simulation of 1.3- μ m oxide-confined in-plane quantum-dot (InGa)As/GaAs lasers. Optical and Quantum Electronics, 2003, 35, 675-692.	1.5	6
134	Nitride VCSEL design for continuous-wave operation of higher-order optical modes. Applied Physics A: Materials Science and Processing, 2003, 77, 761-768.	1.1	2
135	Structure optimisation of 1.3- μ m (GaIn)(NAs)-GaAs in-plane lasers. IEE Proceedings: Optoelectronics, 2003, 150, 56.	0.8	0
136	Simulation of performance characteristics of GaInNAs vertical-cavity surface-emitting lasers. IEE Proceedings: Optoelectronics, 2003, 150, 83.	0.8	2
137	Output power saturation in InAs/GaAs quantum dot lasers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1351-1354.	0.8	5
138	Higher-Order Transverse Modes in Possible Nitride VCSELs. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 48-51.	0.8	0
139	Design guidelines for fundamental-mode-operated cascade nitride VCSELs. IEEE Photonics Technology Letters, 2003, 15, 495-497.	1.3	4
140	Radial optical confinement in nitride VCSELs. Journal Physics D: Applied Physics, 2003, 36, 2041-2045.	1.3	2
141	<title>Single-photon devices in quantum cryptography</title>. , 2003, 5136, 344.		2
142	<title>Simulation of threshold operation of GaInNAs diode lasers</title>. , 2003, 5136, 359.		1
143	<title>Designing of possible structures of nitride vertical-cavity surface-emitting lasers</title>. , 2003, 5136, 325.		0
144	Temperature-enhanced radial current spreading in possible VCSEL structures of nitride lasers. Semiconductor Science and Technology, 2002, 17, 255-260.	1.0	3

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145	A novel diagonal-current injection VCSEL design proposed for nitride lasers. Semiconductor Science and Technology, 2001, 16, 598-602.	1.0	7
146	Transverse modes in gain-guided vertical-cavity surface-emitting lasers. Optics Communications, 1998, 148, 63-69.	1.0	32
147	The spatial hole burning effect in gain-guided vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 1998, 31, L11-L15.	1.3	8
148	Carrier diffusion inside active regions of gain-guided vertical-cavity surface-emitting lasers. IEE Proceedings: Optoelectronics, 1997, 144, 421-425.	0.8	18
149	<title>Effects of carrier diffusion on thermal properties of proton-implanted top-surface-emitting lasers</title>. , 1995, , .		4
150	Finite-element thermal model for buried-heterostructure diode lasers. Optical and Quantum Electronics, 1994, 26, 87-95.	1.5	8
151	Thermal analysis of oxide-isolated stripe diode lasers. Journal of Thermal Analysis, 1992, 38, 1447-1462.	0.7	1
152	An appreciation of usability of the finite element method for the thermal analysis of stripe-geometry diode lasers. Journal of Thermal Analysis, 1990, 36, 1171-1189.	0.7	15
153	Finite-element comprehensive thermal modeling of proton-implanted top-surface-emitting lasers. , 0, , .		0
154	(InGa)As/GaAs quantum-dot diode lasers for 1.3-Î¼m optical fibre communication. , 0, , .		0
155	Comparative analysis of possible VCSEL designs for the long-wavelength optical-fibre communication. , 0, , .		0
156	Mode selectivity in oxide-confined vertical-cavity surface-emitting lasers. , 0, , .		0
157	Optical Design of Vertical-Cavity Lasers. , 0, , 447-466.		0